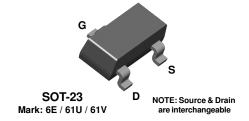


2N5460 2N5461 2N5462 MMBF5460 MMBF5461 MMBF5462





P-Channel General Purpose Amplifier

This device is designed primarily for low level audio and general purpose applications with high impedance signal sources. Sourced from Process 89.

Absolute Maximum Ratings* TA = 25 ℃ unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	- 40	V
V_{GS}	Gate-Source Voltage	40	V
I_{GF}	Forward Gate Current	10	mA
T _J ,T _{sta}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

Thermal Characteristics TA = 25 °C unless otherwise noted

Symbol	Characteristic	Max Units		Units
		2N5460-5462	*MMBF5460-5462	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

P-Channel General Purpose Amplifier

60

115

nV/√Hz

(continued)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
OFF CHA	RACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = 10 \mu A, V_{DS} = 0$	40			V
Igss	Gate Reverse Current	V _{GS} = 20 V, V _{DS} = 0 V _{GS} = 20 V, V _{DS} = 0, T _A = 100°C			5.0 1.0	nA μA
$V_{\text{GS(off)}}$	Gate-Source Cutoff Voltage	V _{DS} = 15 V, I _D = 1.0 μA 5460 5461 5462	0.75 1.0 1.8		6.0 7.5 9.0	V
V _{GS}	Gate-Source Voltage	V _{DS} = 15 V, I _D = 0.1 mA 5460 V _{DS} = 15 V, I _D = 0.2 mA 5461 V _{DS} = 15 V, I _D = 0.4 mA 5462	0.5 0.8 1.5		4.0 4.5 6.0	V V V
ON CHAR	ACTERISTICS Zero-Gate Voltage Drain Current*	V _{DS} = 15 V, V _{GS} = 0 5460 5461	- 1.0 - 2.0		- 5.0 - 9.0	mA mA
		5462	- 4.0		- 16	mA
SMALL SI gfs	GNAL CHARACTERISTICS Forward Transfer Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz 5460 5461	1000 1500		4000 5000	μmho μmho
		5462	2000		6000	μmho
g _{os}	Output Conductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$			75	μmho
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$		5.0	7.0	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz		1.0	2.0	pF
	T	V 45 V V 0		1.0	2.5	٦D
NF	Noise Figure	$V_{DS} = 15 \text{ V}, V_{GS} = 0,$ $R_G = 1.0 \text{ megohm}, f = 100 \text{ Hz},$ BW = 1.0 Hz		1.0	2.5	dB

V_{DS} = 15 V, V_{GS} = 0, f = 100 Hz, BW = 1.0 Hz

en

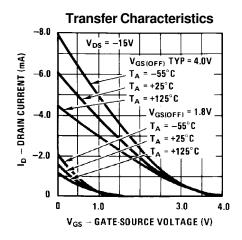
Equivalent Short-Circuit Input Noise Voltage

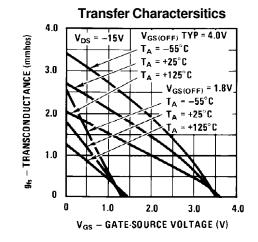
^{*}Pulse Test: Pulse Width \leq 300 ms, Duty Cycle \leq 2%

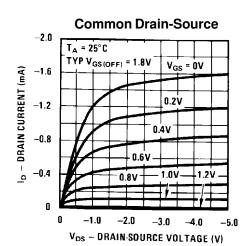
P-Channel General Purpose Amplifier

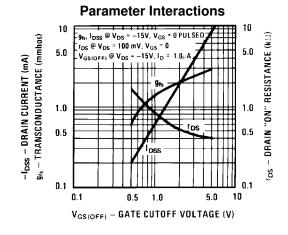
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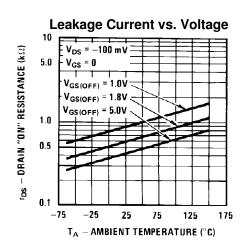
Typical Characteristics (continued)

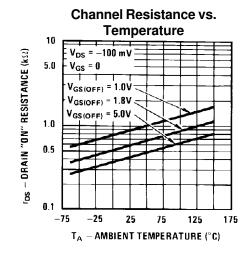








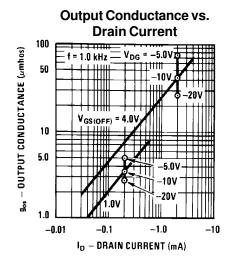


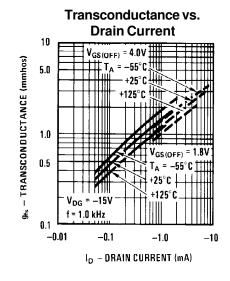


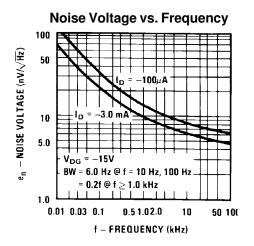
P-Channel General Purpose Amplifier

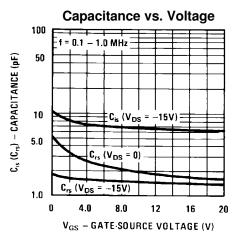
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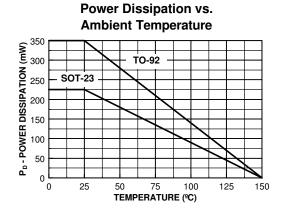
Typical Characteristics (continued)











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